



IN THE SPECIFICATION

Please replace the title of the specification with the following title:

-- Bipolar Junction Transistor with Electrical Hole Isolator--

Please replace the paragraph beginning on page 6, line 5 with the follow rewritten paragraph ;

B1
-- Figure 2a illustrates a cross-sectional view of a preferred embodiment PNP transistor 20 after some initial fabrication steps. In Figure 2a, transistor 20 is formed from a p-type substrate 22 which, due to its conductivity type, is labeled generally with a P designation. An n-type buried layer 24 is formed overlying p-type substrate 22, and due to its conductivity type layer 24 is labeled generally with an N designation. N-type buried layer 24 is preferably formed by masking the upper surface of substrate 22 and then implanting an appropriate n-type dopant, such as arsenic or antimony, into that upper surface. By way of a preferred example, the antimony is implanted at a dosage of $5e^{15}/cm^2$ and at an energy of 60 keV. Note that the doping concentration is relatively high and, thus, n-type buried layer 24 is labeled with an N+ designation. In addition, a subsequent diffusion step is performed after the implant, such as by way of a heating (e.g., annealing) process. Finally, note that layer 24 is referred to as a "buried layer" instead of a well because an additional semiconductor layer is formed on top of it as shown in later figures. However, the phrase "buried layer" should not unnecessarily limit the range of the inventive scope and, indeed, a layer of the type as layer 24 may be referred to in the art using other terminology. To the extent that other terms are consistent with the formation and function of buried layer 24 as described in this document, then they too are intended within the present inventive scope. --

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